

What is claimed is:

1. A method of depositing a wiring thin film on a semiconductor substrate, comprising the steps of:

depositing a Ti film; and

5 depositing an Al-Si-Cu film on the Ti film at a temperature of at least 400°C.

2. A method of depositing a wiring thin film on a semiconductor substrate, comprising the steps of:

depositing a Ti film;

10 depositing an Al-Si-Cu film on the Ti film; and

annealing the semiconductor substrate at a temperature of at least 400°C.

3. The method of depositing a wiring thin film on a semiconductor substrate as disclosed in claim 1, comprising the steps of:

15 depositing a Ti film;

depositing an Al₃Ti film on the Ti film;

and depositing an Al-Si-Cu film on the Al₃Ti film at a temperature of at least 400°C.

20 4. The method of depositing a wiring thin film on a semiconductor substrate as disclosed in claim 2, comprising the steps of:

depositing a Ti film;

depositing an Al₃Ti film on the Ti film;

depositing an Al-Si-Cu film on the Al₃Ti film; and

25 annealing the semiconductor substrate at a temperature of at least 400°C.

5. A method of depositing a wiring thin film on a semiconductor substrate, comprising the steps of:

depositing a Ti film;

30 depositing an Al-Si-Cu film on the Ti film; and

depositing an Al₃Ti film on the Al-Si-Cu film.

6. The method of depositing a wiring thin film on a semiconductor substrate as disclosed in claim 5, comprising the steps of:

- 5 depositing a Ti film;
 depositing an Al-Si-Cu film on the Ti film; and
 depositing an Al₃Ti film on the Al-Si-Cu film; and
 annealing the semiconductor substrate at a temperature of at least 400°C.

10 7. The method of depositing a wiring thin film on a semiconductor substrate as disclosed in claim 5, comprising the steps of:

- depositing a Ti film;
 depositing an Al-Si-Cu film on the Ti film; and
 depositing an on the Al-Si-Cu film at a temperature of at least 400°C.

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